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<p style="text-align: center;">INFORMATION DISCLOSURE CITATION PAGE 1 OF 1</p>				Atty Docket No. OPE-002		Serial No. 09/556,285	
				Applicant G. Taylor			
				Filed April 24, 2000		Group 2811	
US PATENT DOCUMENTS							
Examiner Initials		Document No.	Date	Name	Class	Sub-class	Filing date if approp.
<i>8/27/96</i>	A	4,806,997	2/21/89	Simmons et al.	357	16	
<i>1</i>	B	4,827,320	5/2/89	Morkoc et al.	357	22	
<i>1</i>	C	4,899,200	2/6/90	Shur et al.	357	30	
<i>1</i>	D	5,010,374	4/23/91	Cooke et al.	357	16	
<i>1</i>	E	5,202,896	4/13/93	Taylor	372	50	
<i>1</i>	F	5,422,501	6/6/95	Bayraktaroglu	257	195	
<i>1</i>	G	5,698,900	12/16/97	Bozada et al.	257	744	
<i>8/27/96</i>	H	6,031,243	2/29/00	Taylor	257	13	
<i>1</i>	I						
<i>1</i>	J						
<i>1</i>	K						
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)							
<i>1</i>	1	Kodak CCD-Primer, Charge-Coupled Device (CCD) Image Sensors, Eastman Kodak Company Microelectronics Technology Division, Rochester, NY, pp. KGP-001					
<i>1</i>		1-13 Publication data not provided					
<i>8/27/96</i>	2	Lee H., Wicks G. & Eastman L.F., High Temperature Annealing of Modulation Doped GaAs/A ₁ GaAs Heterostructures for FET Applications, IEEE/Cornell Conf. on High Speed Semiconductor Devices & Ckts, 8/83, pp. 204 - 208					
<i>8/27/96</i>	3	Taylor G. & Simmons J., Heterojunction Field-Effect Transistor (HFET), Electronics Letters, 17th July 1986, Vol 22, No. 15, pp. 784-786					
<i>8/27/96</i>	4	Cates C., Serapiglia B., Dora Y., et al., Detection of Terahertz Light with Intersubband Transition in Semiconductor Quantum Wells, University of California Publication data not provided					
EXAMINER <i>G. Munson</i>				DATE CONSIDERED <i>25 OCTOBER 2002</i>			